

20V Dual P-Channel MOSFET



TSSOP-8

Pin Definition:

1

1. Drain 1 8. Drain 2 2. Source 1 7. Source 2 3. Source 1 6. Source 2

4. Gate 1 5. Gate 2

PRODUCT SUMMARY

V _{DS} (V)	$V_{DS}(V)$ $R_{DS(on)}(m\Omega)$		
-20	30 @ V _{GS} = -4.5V	-4.5	
	42 @ V _{GS} = -2.5V	-3	
	68 @ V _{GS} = -1.8V	-2	

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

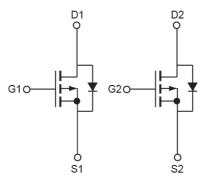
- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing
TSM6963SDCA RVG	TSSOP-8	3Kpcs / 13" Reel

Note: "G" denote for Halogen Free Product

Block Diagram



Dual P-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	-20	V	
Gate-Source Voltage		V_{GS}	±12	V	
Continuous Drain Current, V _{GS} @4.5V.		I _D	-4.5	Α	
Pulsed Drain Current, V _{GS} @4.5V		I _{DM}	-16	Α	
Continuous Source Current (Diode Cond	uction) ^{a,b}	I _S	-1.0	Α	
Mariana Para Pinainatian	Ta = 25°C		1.14	\A/	
Maximum Power Dissipation	Ta = 70°C	P_{D}	0.73	W	
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Foot (Drain) Thermal Resistance	$R\Theta_{JF}$	75	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	R⊖ _{JA}	90	°C/W

Notes:

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature



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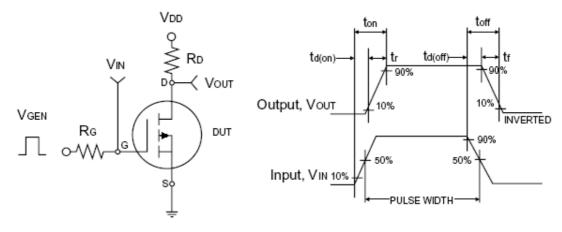


Electrical Specifications (Ta =25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static		1				
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = -250uA$	BV _{DSS}	-20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = -250$ uA	$V_{GS(TH)}$	-0.5	-0.7	-1.0	V
Zero Gate Voltage Drain Current	$V_{DS} = -16V, V_{GS} = 0V$	I _{DSS}			-1	uA
Gate Body Leakage	$V_{GS} = \pm 12V$, $V_{DS} = 0V$	I _{GSS}			±100	nA
On-State Drain Current	$V_{DS} = -5V, V_{GS} = -4.5V$	I _{D(ON)}	-25			Α
	$V_{GS} = -4.5V$, $I_{D} = -4.5A$			23	30	mΩ
Drain-Source On-State Resistance	$V_{GS} = -2.5V, I_{D} = -3A$	R _{DS(ON)}		30	42	
	$V_{GS} = -1.8V, I_{D} = -2A$			45	68	
Forward Transconductance	$V_{DS} = -5V, I_{D} = -4.5A$	g fs		16		S
Diode Forward Voltage	I _S =-0.5A, V _{GS} =0V	V_{SD}		- 0.8	-1.3	V
Dynamic ^b						
Total Gate Charge	V _{DS} =-10V, I _D =-4.5A,	Q_g		14	20	
Gate-Source Charge	, , ,	Q_gs		2.1	10	nC
Gate-Drain Charge	V _{GS} =-4.5 V	$Q_{GS} = -4.5V$ Q_{gd}		4.7		
Input Capacitance	- V _{DS} =-10V, V _{GS} =0V, - f =1.0MHz	C_{iss}		1500		
Output Capacitance		C _{oss}		220		pF
Reverse Transfer Capacitance		C _{rss}		160		
Switching ^{b,C}						
Turn-On Delay Time	$\begin{array}{c} - \\ - \\ - \\ - \\ - \\ - \\ - \\ - \\ - \\ - $	t _{d(on)}		6	11	
Turn-On Rise Time		t _r		13	23	20
Turn-Off Delay Time		t _{d(off)}		86	145	nS
Turn-Off Fall Time		t _f		42	70	

Notes:

- a. pulse test: PW $\leq 300\mu$ S, duty cycle $\leq 2\%$
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

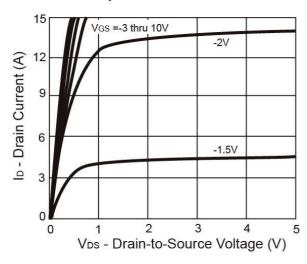


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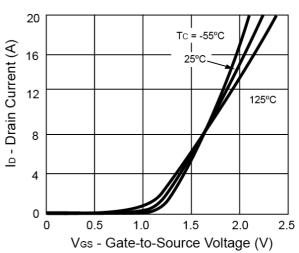


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

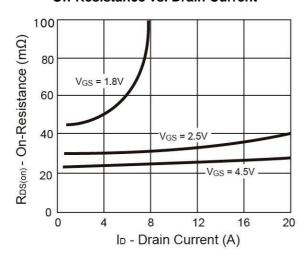
Output Characteristics



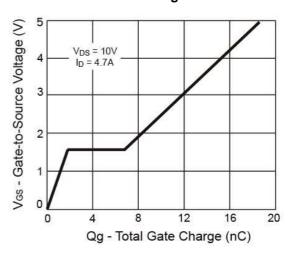
Transfer Characteristics



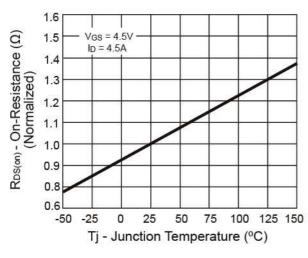
On-Resistance vs. Drain Current



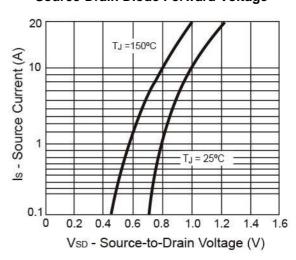
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



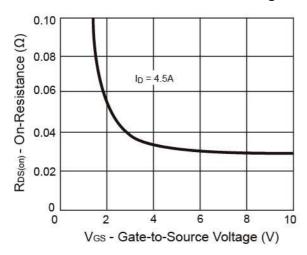


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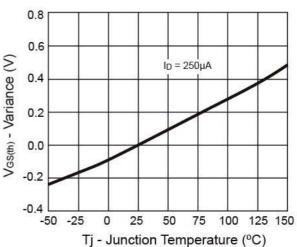


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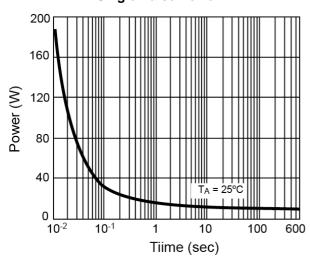
On-Resistance vs. Gate-Source Voltage



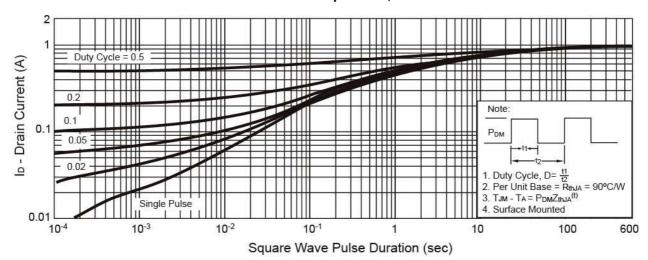
Threshold Voltage



Single Pulse Power



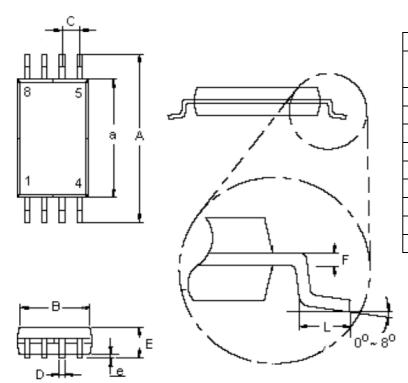
Normalized Thermal Transient Impedance, Junction-to-Ambient



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TSSOP-8 Mechanical Drawing



TSSOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
Α	6.20	6.60	0.244	0.260	
а	4.30	4.50	0.170	0.177	
В	2.90	3.10	0.114	0.122	
С	0.65 (typ)		0.025 (typ)		
D	0.25	0.30	0.010	0.019	
Е	1.05	1.20	0.041	0.049	
е	0.05	0.15	0.002	0.009	
F	0.127		0.005		
L	0.50	0.70	0.020	0.028	

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product

 $oldsymbol{O}$ =Jan $oldsymbol{P}$ =Feb $oldsymbol{Q}$ =Mar $oldsymbol{R}$ =Apr

 $S = May \quad T = Jun \quad U = Jul \quad V = Aug$

W =Sep X =Oct Y =Nov Z =Dec

L = Lot Code



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